

Applicant: Ping-Hsu Chen, et al.
Serial No.: 10/786,187
Filing Date: 02/25/2004
Attorney Docket No.: 67,200-1070

IN THE CLAIMS

Please amend claims 1, 3, 6, 8, 9, 11, 14 and 16 as follows.

1. (Currently amended) A method of exposing alignment marks on a substrate having at least one transparent dielectric layer overlaying the alignment marks and at least one opaque layer overlaying the alignment marks at least one transparent dielectric layer, comprising the steps of:

providing a focused ion beam; and

exposing rendering visible the alignment marks by impinging said focused ion beam against the at least one opaque layer to obliterate the at least one opaque layer substantially overlaying the alignment marks; and

leaving at least a portion of the at least one transparent layer intact over the alignment marks.

2. (Original) The method of claim 1 wherein said focused ion beam has a noble gas ion source.

3. (Currently amended) The method of claim 1 wherein said focused ion beam has a current density of about 200-800 400-800 pA.

BEST AVAILABLE COPY

Applicant: Ping-Hsu Chen, et al.
Serial No.: 10/786,187
Filing Date: 02/25/2004
Attorney Docket No.: 67,200-1070

4. (Original) The method of claim 3 wherein said focused ion beam has a noble gas ion source.

5. (Original) The method of claim 2 wherein said noble gas ion source comprises argon.

6. (Currently amended) The method of claim 5 wherein said focused ion beam has a current density of about ~~200-800~~ 400-800 pA.

7. (Original) The method of claim 4 wherein said noble gas ion source comprises argon.

8. (Currently amended) The method of claim 7 wherein said focused ion beam has a current density of about ~~200-800~~ 400-800 pA.

9. (Currently amended) A method of exposing alignment marks on a substrate having at least one transparent dielectric layer overlaying the alignment marks and at least one opaque layer overlaying the alignment marks at least one transparent dielectric layer, comprising the steps of:

Applicant: Ping-Hsu Chen, et al.

Serial No.: 10/786,187

Filing Date: 02/25/2004

Attorney Docket No.: 67,200-1070

providing a focused ion beam; and

cutting an exposure opening in the at least one opaque layer to ~~expose~~ render visible the alignment marks by impinging said focused ion beam against the at least one opaque layer; and

leaving the at least one transparent layer intact over the alignment marks.

10. (Original) The method of claim 9 wherein said focused ion beam has a noble gas ion source.

11. (Currently amended) The method of claim 9 wherein said focused ion beam has a current density of about ~~200-800~~ 400-800 pA.

12. (Original) The method of claim 11 wherein said focused ion beam has a noble gas ion source.

13. (Original) The method of claim 10 wherein said noble gas ion source comprises argon.

14. (Currently amended) The method of claim 13 wherein said focused ion beam has a current density of about

Applicant: Ping-Rsu Chen, et al.
Serial No.: 10/786,187
Filing Date: 02/25/2004
Attorney Docket No.: 67,200-1070
~~200-800~~ 400-800 pA.

15. (Original) The method of claim 12 wherein said noble gas ion source comprises argon.

Applicant: Ping-Hsu Chen, et al.

Serial No.: 10/786,187

Filing Date: 02/25/2004

Attorney Docket No.: 67,200-1070

16. (Currently amended) A method of exposing alignment marks on a substrate having a transparent dielectric layer overlaying the alignment marks and at least one opaque layer overlying the dielectric layer, comprising the steps of:

providing a focused ion beam; ~~and~~

cutting an exposure opening in the at least one opaque layer to the dielectric layer to ~~visually-expose~~ render visible the alignment marks by impinging said focused ion beam against the at least one opaque layer;

leaving at least a portion of the dielectric layer intact over the alignment marks; and

viewing the alignment marks through the exposure opening and the dielectric layer.

17. (Original) The method of claim 16 wherein said focused ion beam has a noble gas ion source.

18. (Original) The method of claim 16 wherein said focused ion beam has a current density of about 200-800 pA.

19. (Original) The method of claim 17 wherein said noble gas ion source comprises argon.

Applicant: Ping-Hsu Chen, et al.

Serial No.: 10/786,187

Filing Date: 02/25/2004

Attorney Docket No.: 67,200-1070

20. (Original) The method of claim 19 wherein said focused ion beam has a current density of about 200-800 pA.

**This Page is Inserted by IFW Indexing and Scanning
Operations and is not part of the Official Record**

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images include but are not limited to the items checked:

- ☐ **BLACK BORDERS**
- ☐ **IMAGE CUT OFF AT TOP, BOTTOM OR SIDES**
- ☐ **FADED TEXT OR DRAWING**
- ☐ **BLURRED OR ILLEGIBLE TEXT OR DRAWING**
- ☐ **SKEWED/SLANTED IMAGES**
- ☐ **COLOR OR BLACK AND WHITE PHOTOGRAPHS**
- ☐ **GRAY SCALE DOCUMENTS**
- ☐ **LINES OR MARKS ON ORIGINAL DOCUMENT**
- ☐ **REFERENCE(S) OR EXHIBIT(S) SUBMITTED ARE POOR QUALITY**
- ☐ **OTHER:** _____

IMAGES ARE BEST AVAILABLE COPY.

As rescanning these documents will not correct the image problems checked, please do not report these problems to the IFW Image Problem Mailbox.